

Features

- 100V/273A,
 $R_{DS(on)} = 2m\Omega (Typ.) @ V_{GS} = 10V$
- Excellent $Q_G \times R_{DS(on)}$ product(FOM)
- SGT Technology
- High Ruggedness
- 100% Avalanche Tested

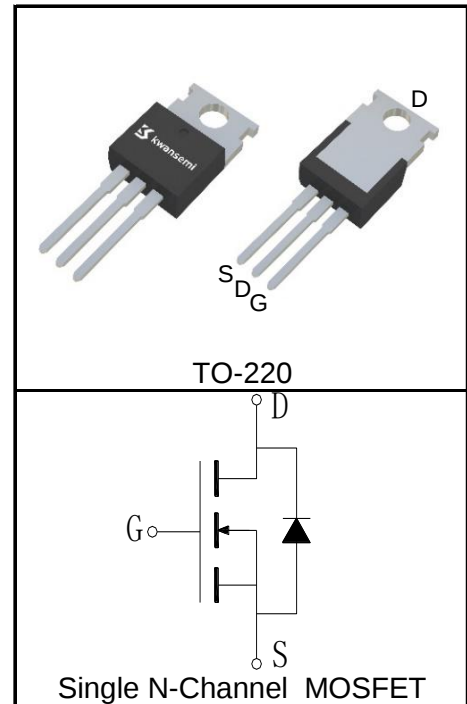
Applications

- Motor Control
- Battery Power Management



Halogen-Free

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	V
T_{Jmax}	Maximum Junction Temperature	175	$^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 175	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C = 25^\circ\text{C}$ 273	A
Mounted on Large Heat Sink			
$I_{DP}^{(1)}$	Pulse Drain Current	$T_C = 25^\circ\text{C}$ 1092	A
$I_D^{(2)}$	Continuous Drain Current ($V_{GS} = 10V$)	$T_C = 25^\circ\text{C}$ 273	A
		$T_C = 100^\circ\text{C}$ 193	
P_D	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$ 357	W
		$T_C = 100^\circ\text{C}$ 178	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.42	$^\circ\text{C/W}$
$R_{\theta JA}^{(3)}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ\text{C/W}$
Drain-Source Avalanche Ratings			
$E_{AS}^{(4)}$	Avalanche Energy, Single Pulsed	1640	mJ

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	Rating			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V			1	μA
			T _J =125°C		30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =40A		2	2.4	mΩ
		V _{GS} =6V, I _{DS} =20A		2.8	3.6	mΩ
Diode Characteristics						
V _{SD} ⑤	Diode Forward Voltage	I _{SD} =40A, V _{GS} =0V		0.83	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =40A, dI _{SD} /dt=100A/μs		77		ns
Q _{rr}	Reverse Recovery Charge			171		nC
Dynamic Characteristics ⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		2		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =50V, Frequency=200KHz		10800		pF
C _{oss}	Output Capacitance			1370		
C _{rss}	Reverse Transfer Capacitance			50		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =50V, I _{DS} =40A, V _{GEN} =10V, R _G =3Ω		37		ns
t _r	Turn-on Rise Time			29		
t _{d(OFF)}	Turn-off Delay Time			86		
t _f	Turn-off Fall Time			43		
Gate Charge Characteristics ⑥						
Q _g	Total Gate Charge	V _{DS} =50V, V _{GS} =10V, I _{DS} =40A		174		nC
Q _{gs}	Gate-Source Charge			46		
Q _{gd}	Gate-Drain Charge			46		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 75A.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , Starting $T_J = 25^{\circ}\text{C}$, $I_{ASmax} = 81A$, $L = 0.5\text{mH}$, $V_{DD} = 48V$, $R_G = 25\Omega$, $V_{GS} = 10V$. Part not recommended for use above this value. 100% Final Test at $I_{AS} = 56A$, $L = 0.5\text{mH}$.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

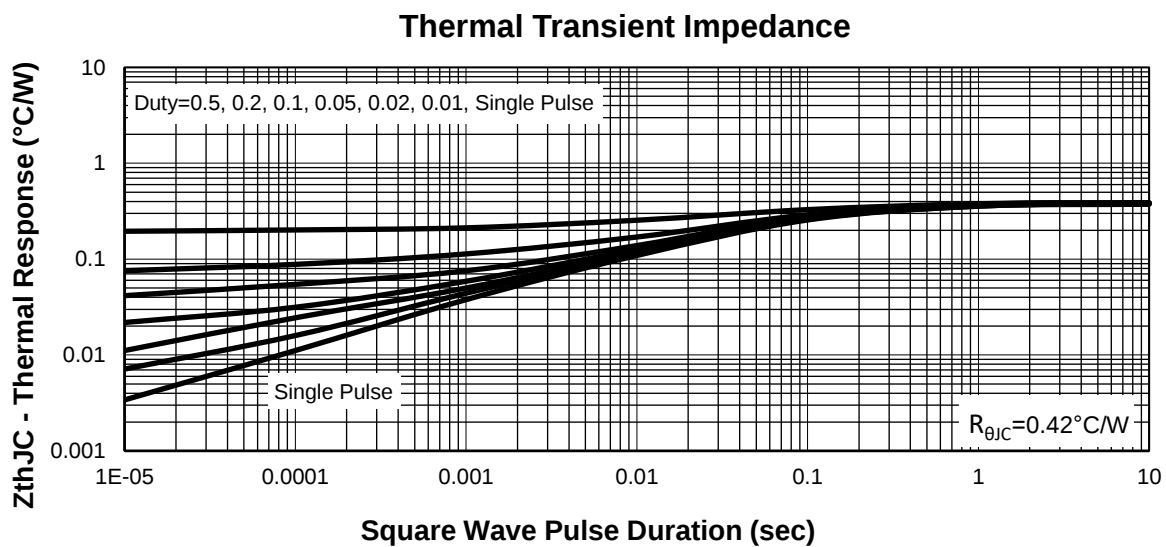
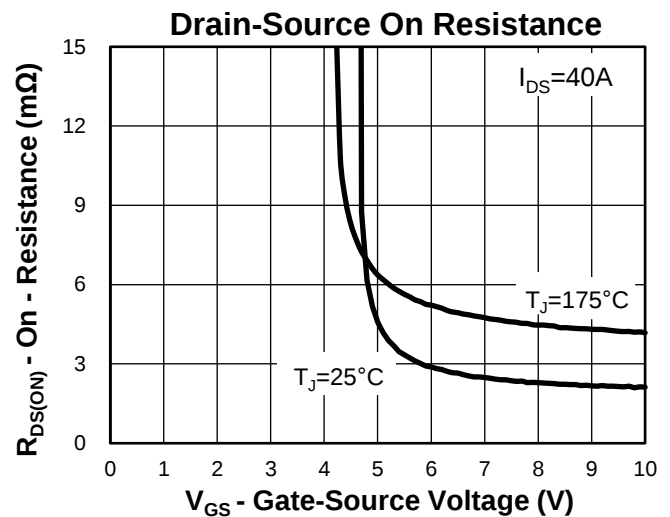
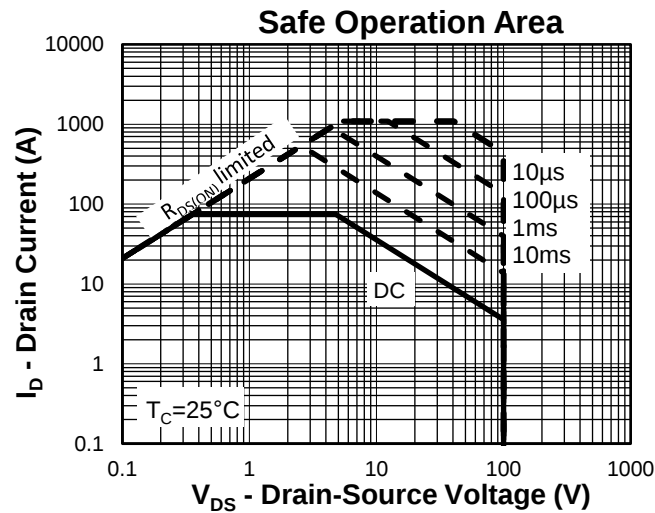
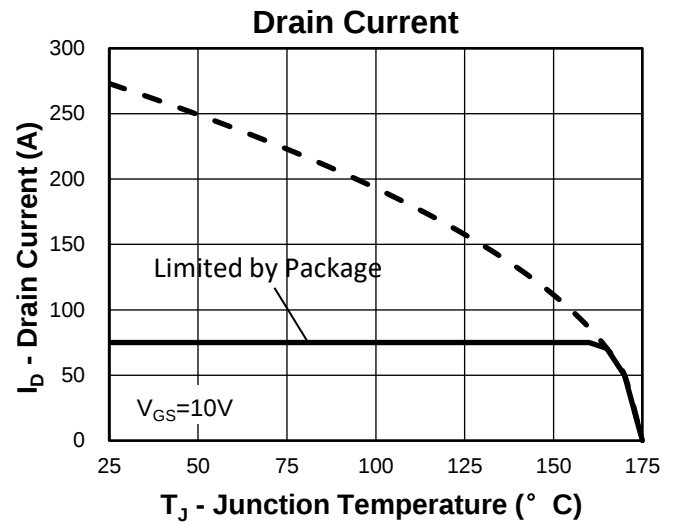
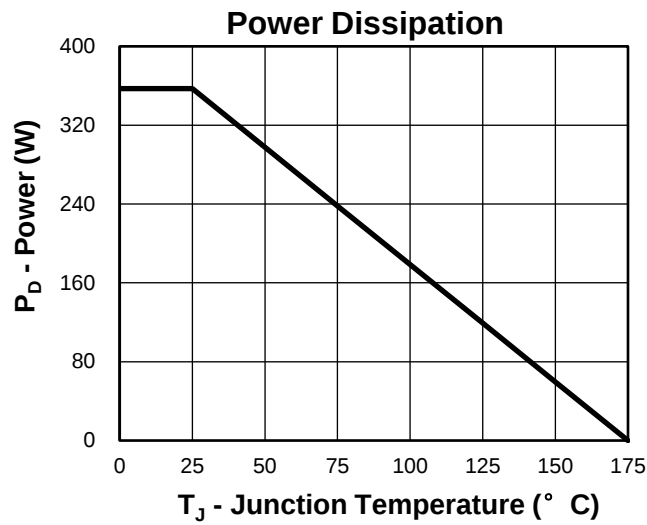
Ordering and Marking Information

Device	Package	Packaging	Quantity	Reel Size	Tape width
KS12012CAT	TO-220	Tube	50	-	-

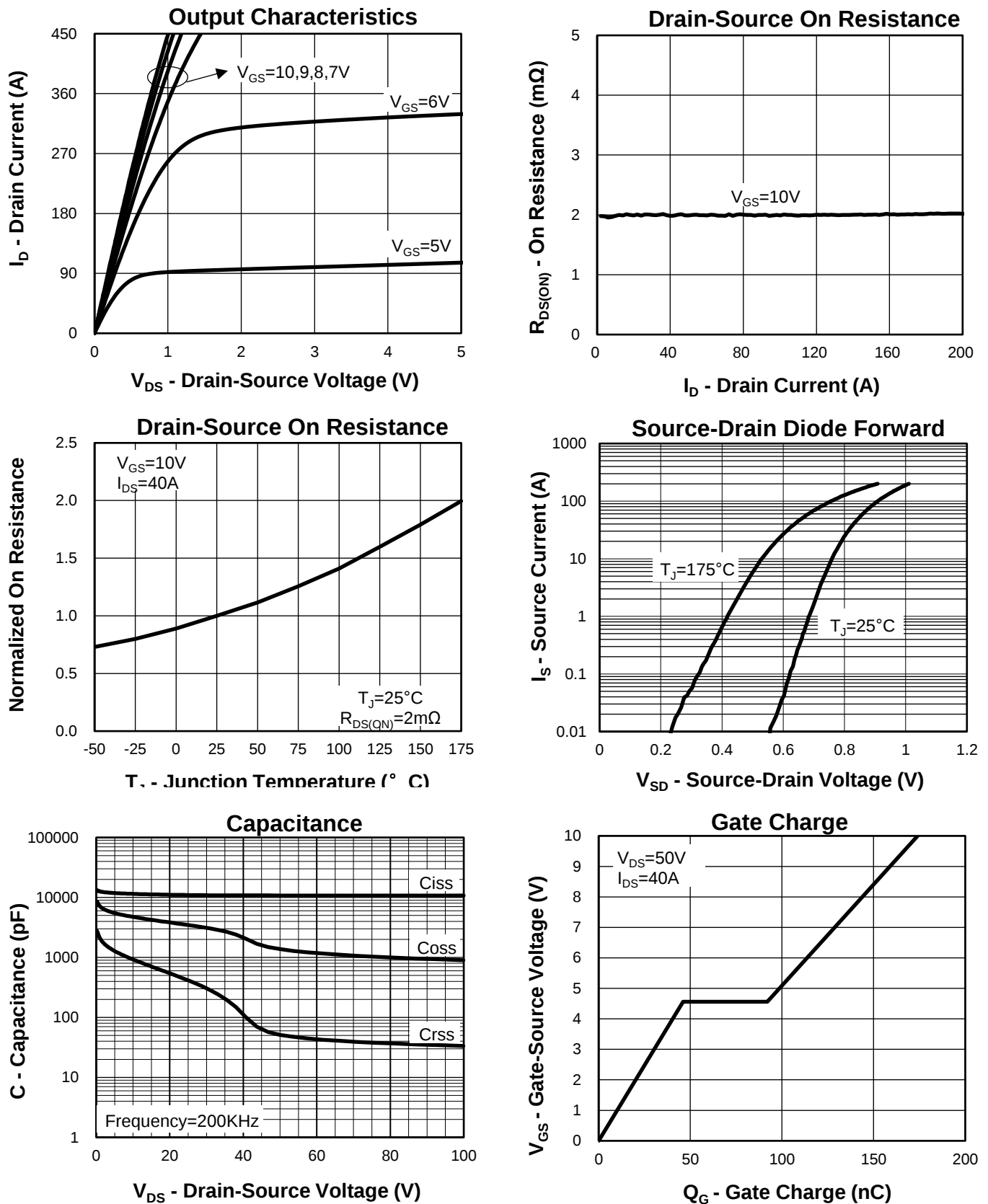


1st Line: Kwansemi LOGO, Kwansemi Code(KS)
2nd Line: Part Number(12012T)
3rd Line: Lot Number(YWWXXX)

Typical Characteristics

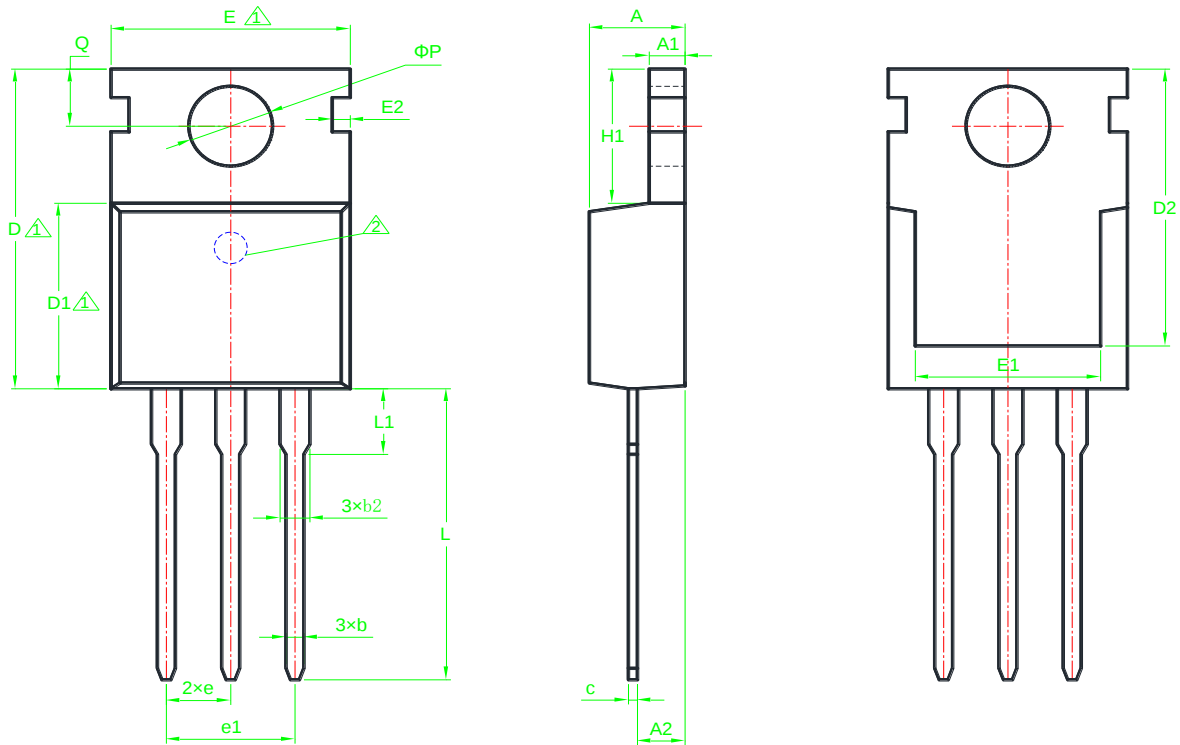


Typical Characteristics



Package Information

TO-220

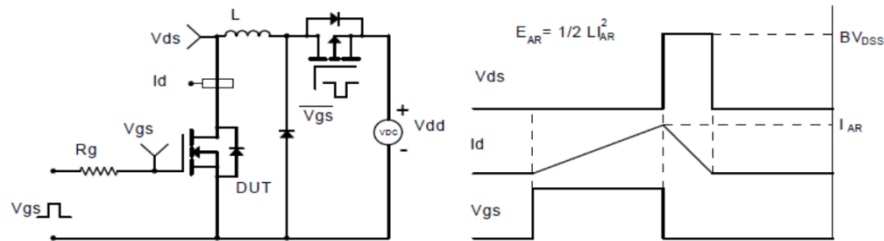


SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.30	4.55	4.80	0.169	0.179	0.189	E1	7.00	*	8.40	0.276	*	0.331
A1	1.20	1.30	1.45	0.047	0.051	0.057	E2	*	*	0.75	*	*	0.030
A2	2.20	2.40	2.70	0.087	0.094	0.106	e	2.54BSC			0.100BSC		
b	0.70	0.80	0.95	0.028	0.031	0.037	e1	5.08BSC			0.200BSC		
b2	1.15	1.35	1.50	0.045	0.053	0.059	H1	6.30	6.50	6.80	0.248	0.256	0.268
c	0.40	0.50	0.60	0.016	0.020	0.024	L	12.70	13.20	13.90	0.500	0.520	0.547
D	15.10	15.60	16.10	0.594	0.614	0.634	L1	2.85	*	3.50	0.112	*	0.138
D1	8.75	9.20	9.65	0.344	0.362	0.380	ØP	3.50	3.65	3.80	0.138	0.144	0.150
D2	12.20	12.50	12.80	0.480	0.492	0.504	Q	2.70	*	2.90	0.106	*	0.114
E	9.70	10.00	10.30	0.382	0.394	0.406							

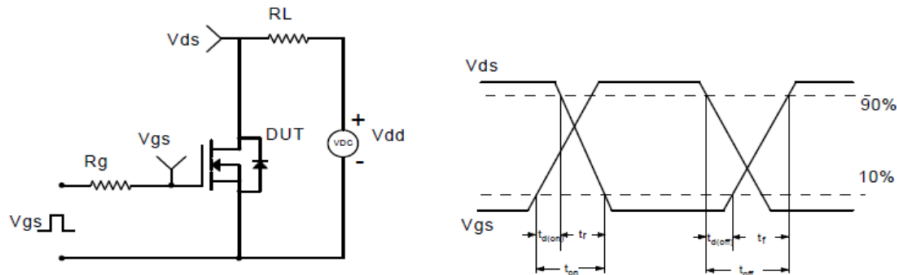
1 Dimensions D and D1 and E do not include mold flash protrusions or gate burrs.

2 The existence and size of demolding hole are variable depending on mold.

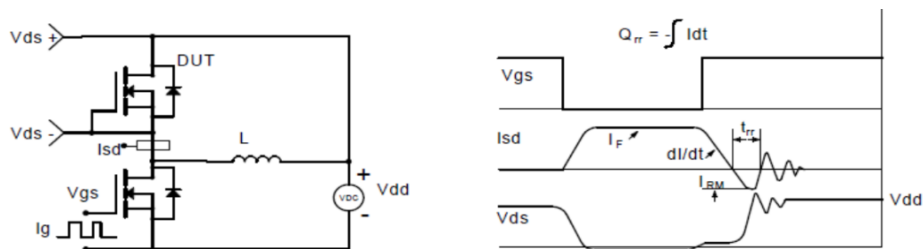
Avalanche Test Circuit and Waveforms



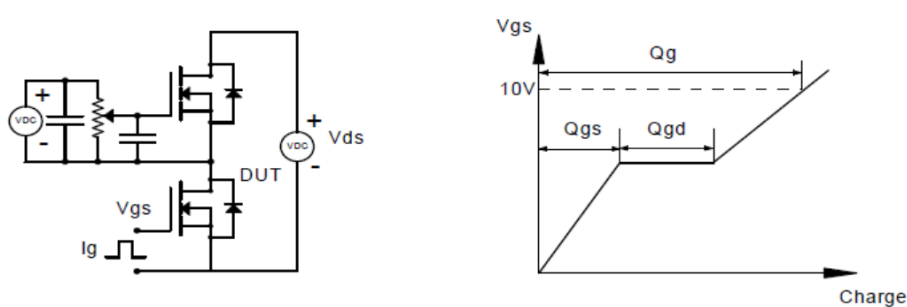
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

Kwansemi Semiconductor Co.,Ltd

Email:Sales@kwansemi.com

Web:www.kwansemi.com

DISCLAIMER:

Kwansemi reserves the right to change the specifications and circuitry without notice at any time. The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.